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Internal Webinar

Study of Interstitial Transition Metal Compound Thin Films

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Numerous ferromagnetic electrode materials with a larger spin polarization ratio and tunneling magnetoresistance (TMR) have been actively investigated for their spintronic applications. In this scenario, an interesting class of promising electrode materials, tetratransition metal nitrides (M₄N; M = Fe, Co, Ni etc.) have recently occupied a privileged position. M4N is reported to exhibit halfmetallicity, high magnetization, ultra-high TMR and tunable magnetic anisotropy with an electric field [1]. All these prerequisite merits make M4N compounds an exceptional class of candidates for next-generation spintronics technologies. However, the some prominent issues are present in these M₄N compounds which limit their applications and that need to be sought. For instance, a large variation in the magnetic behavior in well-established Fe₄N thin films can be seen from the available literature. In this view, we have addressed the unsolved issues present in M4N compounds and attempted to scrutinize them. In this work, a detailed and systematic investigation on the magnetic, structural and electronic properties of transition metal nitride thin films has been carried out.

References:

[1] Nidhi Pandey et.al., Physical Review Materials 3, 114414 (2019).

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